



ShenzhenTaimaoTechnology Co.,Ltd.

TO-92 Plastic-Encapsulate Transistors

2N4126 TRANSISTOR (PNP)

FEATURES

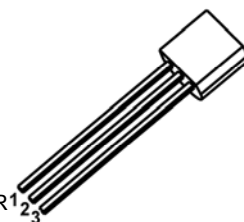
- PNP Silicon Epitaxial Transistor for Switching and Amplifier Applications.
- As Complementary Type, The NPN Transistor 2N4124 is Recommended.

TO - 92

1. EMITTER

2. BASE

3. COLLECTOR



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current	-0.2	A
P_C	Collector Power Dissipation	625	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	200	$^{\circ}\text{C/W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -0.01\text{mA}, I_E = 0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -1\text{mA}, I_B = 0$	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -0.01\text{mA}, I_C = 0$	-4			V
Collector cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-50	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = -3\text{V}, I_C = 0$			-50	nA
DC current gain	$h_{FE(1)}^*$	$V_{CE} = -1\text{V}, I_C = -2\text{mA}$	120		360	
	$h_{FE(2)}^*$	$V_{CE} = -1\text{V}, I_C = -50\text{mA}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}^*$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C = -50\text{mA}, I_B = -5\text{mA}$			-0.95	V
Collector output capacitance	C_{ob}	$V_{CB} = -5\text{V}, I_E = 0, f = 1\text{MHz}$			4.5	pF
Transition frequency	f_T	$V_{CE} = -20\text{V}, I_C = -10\text{mA}, f = 100\text{MHz}$	250			MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycles $\leq 1.5\%$.